

ABSTRACT OF THE DISCLOSURE

There is disclosed a silicon focus ring consisting of silicon single crystal used as a silicon focus ring in a plasma apparatus, wherein concentration of interstitial oxygen contained in the silicon focus ring is not less than  $5 \times 10^{17}$  atoms/cm<sup>3</sup> and not more than  $1.5 \times 10^{18}$  atoms/cm<sup>3</sup>, and a producing method for a silicon focus ring used for a plasma apparatus, wherein a single crystal silicon wherein concentration of interstitial oxygen contained in the silicon focus ring is not less than  $5 \times 10^{17}$  atoms/cm<sup>3</sup> and not more than  $1.5 \times 10^{18}$  atoms/cm<sup>3</sup> is grown by a Czochralski method, the single crystal silicon is processed in a circle, and a silicon focus ring is produced. There can be provided a silicon focus ring, which can prevent disadvantage due to impurities such as heavy metal.